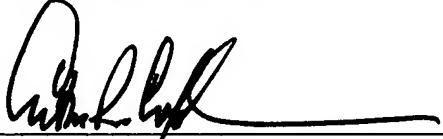


REMARKS

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page(s) is captioned "**Version With Markings To Show Changes Made.**"

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION

Page 1, before the first line, please insert as a separate paragraph:

This application is the US national phase of international application
PCT/GB00/03249 filed 22 August 2000, which designated the US.

IN THE CLAIMS

11. A method of fabricating an electronic device comprising the steps of (a) depositing $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ onto a substrate by a method according to ~~any one of Claims 1 to 10~~; and (b) connecting at least two electrodes to the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$.

14. A method of fabricating a device according to ~~one of Claims 11 or 12~~ wherein the method further comprises the step of growing a passivating layer of CdTe on the $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$.

15. A device obtainable by a method according to ~~one of Claims 11 to 14~~.

16. An infrared detector comprising an array of devices, each device being obtainable by a method according to ~~one of Claims 11 to 14~~.

17. $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ obtainable by a method according to ~~one of Claims 1 to 10~~.